

Features

- Uses CRM(CQ) advanced SkyMOS3 technology
- Extremely low on-resistance RDS(on)
- Excellent QgxRDS(on) product(FOM)
- Qualified according to JEDEC criteria

Product Summary

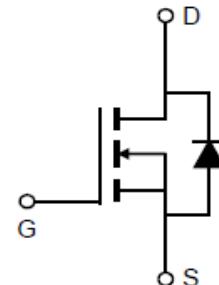
V _{DS}	200V
R _{DS(on)}	13mΩ
I _D	80A

100% Avalanche Tested

100% DVDS Tested

Applications

- Motor control and drive
- Battery management
- UPS (Uninterruptible Power Supplies)



Package Marking and Ordering Information

MARKING	流通码	Package	Packing	Reel Size	Tape Width	Qty
CRSQ155N20N3		TO-247	Tube	N/A	N/A	30pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage T _C = 25°C (Silicon limit) T _C = 25°C (Package limit) T _C = 100°C (Silicon limit)	V _{DS} I _D	200 83 160 52	V A
Pulsed drain current (T _C = 25°C, t _p limited by T _{jmax})	I _D pulse	331	A
Avalanche energy, single pulse (L=0.5mH, R _g =25Ω) ^[1]	E _{AS}	169	mJ
Gate-Source voltage	V _{GS}	±20	V
Power dissipation (T _C = 25°C)	P _{tot}	228	W
Operating junction and storage temperature	T _j , T _{stg}	-55...+150	°C

※. Notes: 1. EAS is tested at starting T_j = 25°C, L = 0.5mH, I_{AS} = 26A, V_{gs}=10V.

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction - case.	R _{thJC}	0.55	°C/W
Thermal resistance, junction - ambient(min. footprint)	R _{thJA}	46	

Electrical Characteristic (at T_j = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV _{DSS}	200	-	-	V	V _{GS} =0V, I _D =250uA
Gate threshold voltage	V _{GS(th)}	2	3	4	V	V _{DS} =V _{GS} , I _D =250uA
Zero gate voltage drain current	I _{DSS}	-	-	1	µA	V _{DS} =200V, V _{GS} =0V T _j =25°C T _j =150°C
Gate-source leakage current	I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
Drain-source on-state resistance	R _{DS(on)}	-	13.0	15.5	mΩ	V _{GS} =10V, I _D =40A
Transconductance	g _{fs}	-	71.9	-	S	V _{DS} =5V, I _D =40A

Dynamic Characteristic

Input Capacitance	C _{iss}	-	3602	-	pF	V _{GS} =0V, V _{DS} =100V, f=1MHz
Output Capacitance	C _{oss}	-	274.5	-		
Reverse Transfer Capacitance	C _{rss}	-	22.3	-		
Gate Total Charge	Q _G	-	56.2	-	nC	V _{GS} =10V, V _{DS} =100V, I _D =40A, f=1MHz
Gate-Source charge	Q _{gs}	-	18.6	-		
Gate-Drain charge	Q _{gd}	-	14.5	-		
Turn-on delay time	t _{d(on)}	-	18.3	-	ns	V _{GS} =10V, V _{DD} =100V, R _{G_ext} =2.7Ω
Rise time	t _r	-	80	-		
Turn-off delay time	t _{d(off)}	-	45.5	-		
Fall time	t _f	-	87.2	-		
Gate resistance	R _G	-	1.9	-	Ω	V _{GS} =0V, V _{DS} =0V, f=1MHz

Body Diode Characteristic



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CRSQ155N20N3

SkyMOS3 N-MOSFET 200V, 13mΩ, 80A

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V _{SD}	-	0.85	1.3	V	V _{GS} =0V, I _{SD} =40A
Body Diode Reverse Recovery Time	t _{rr}	-	131.3	-	ns	I _F =40A, dI/dt=100A/us
Body Diode Reverse Recovery Charge	Q _{rr}	-	585	-	nC	V _{ds} =100V

Typical Performance Characteristics

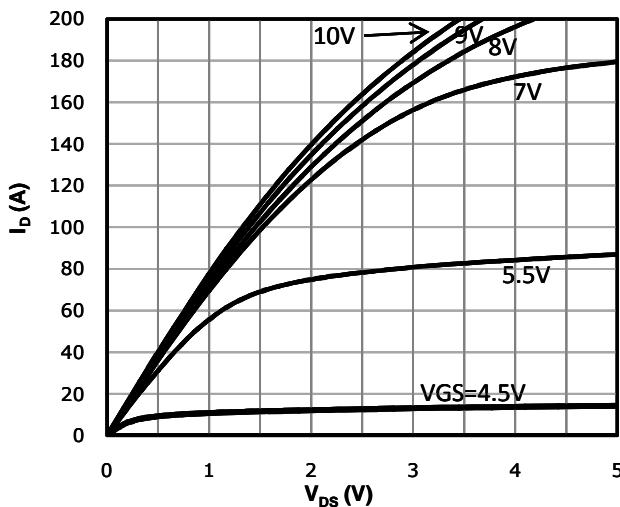
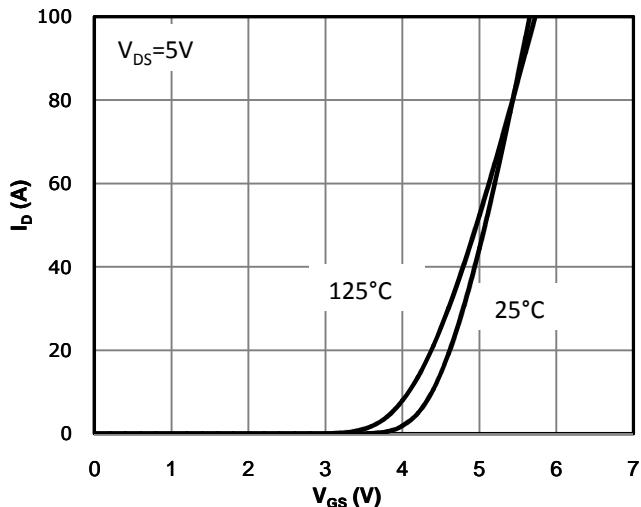
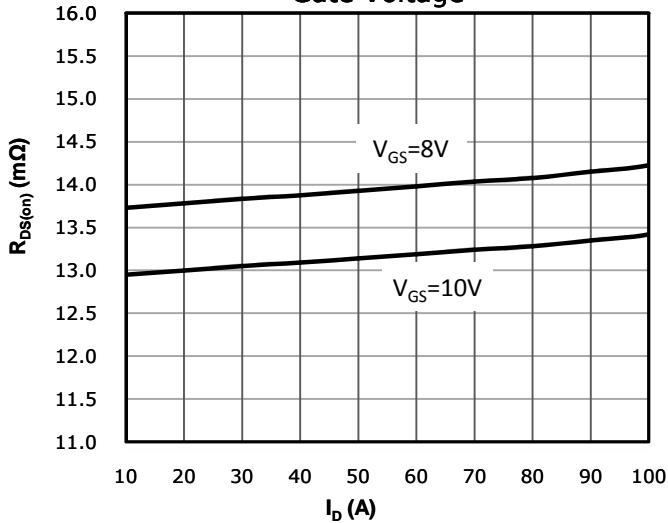
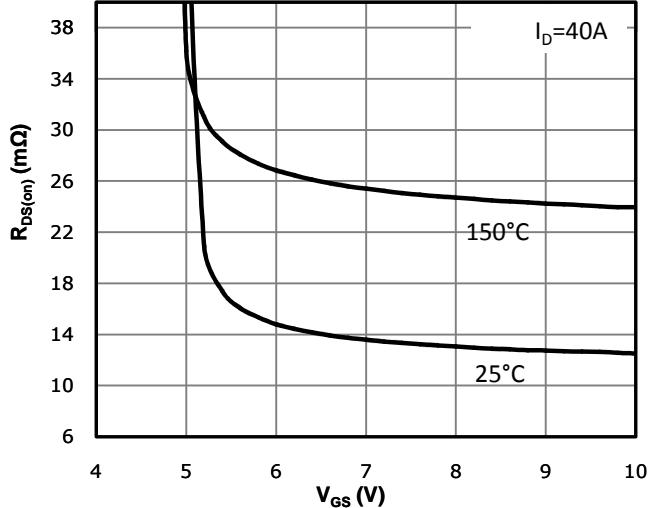
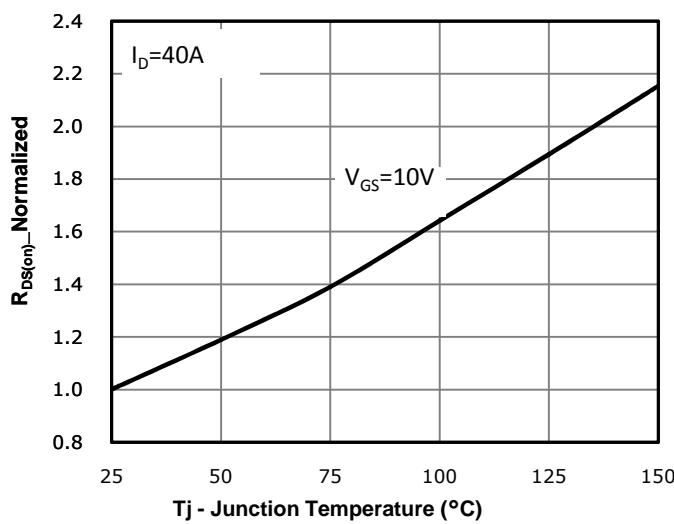
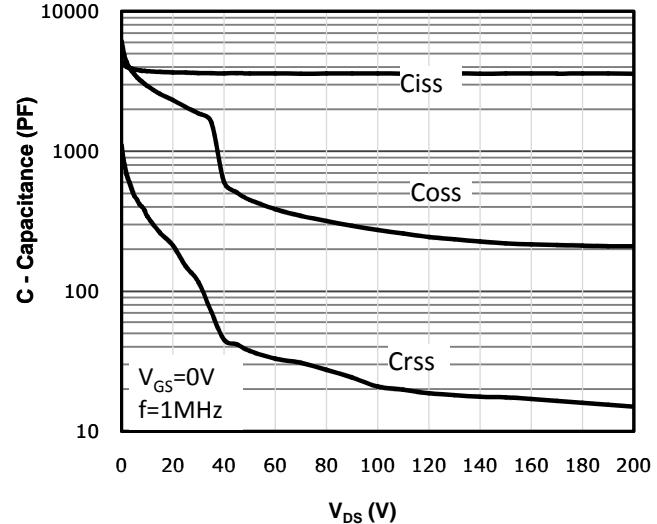
Fig 1: Output Characteristics

Fig 2: Transfer Characteristics

Fig 3: R_{d(on)} vs Drain Current and Gate Voltage

Fig 4: R_{d(on)} vs Gate Voltage

Fig 5: R_{d(on)} vs. Temperature

Fig 6: Capacitance Characteristics


Fig 7: Gate Charge Characteristics

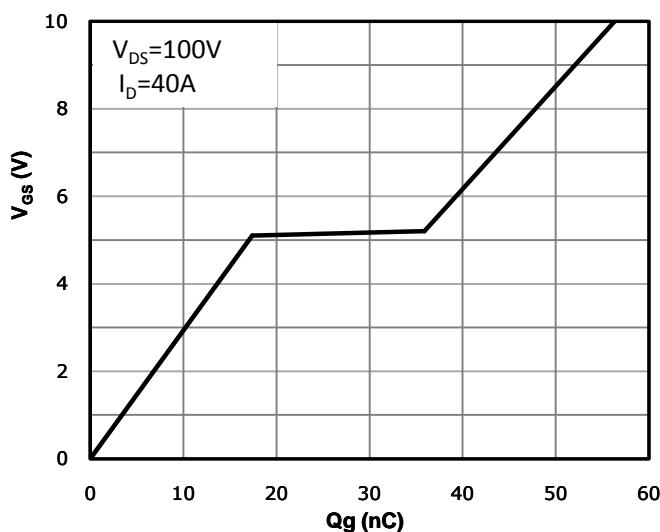


Fig 8: Body-diode Forward Characteristics

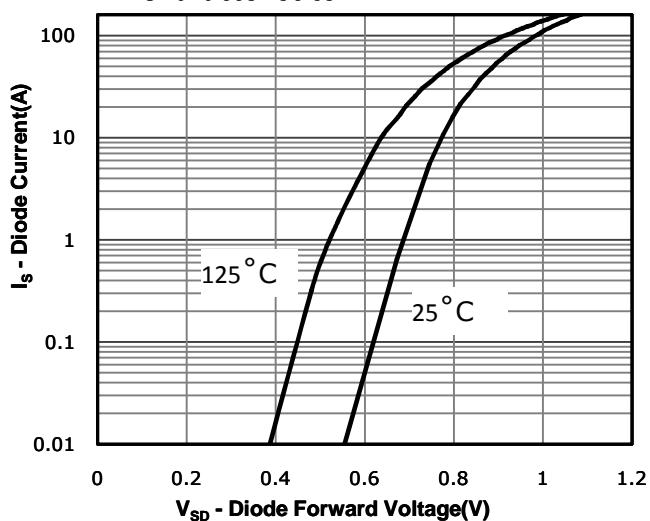


Fig 9: Power Dissipation

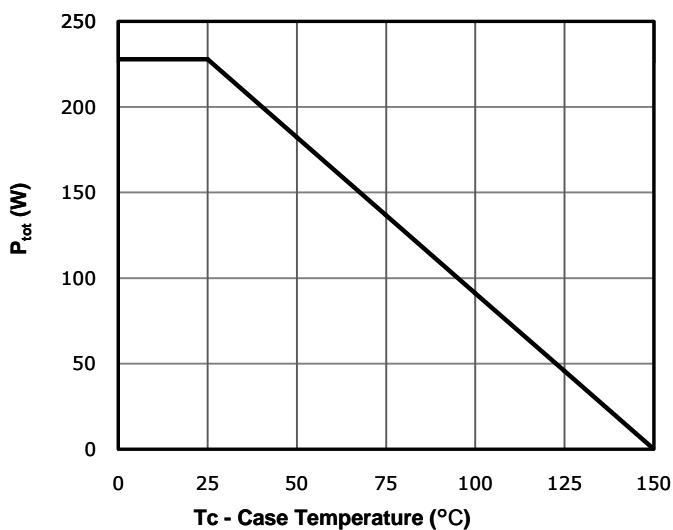


Fig 10: Drain Current Derating

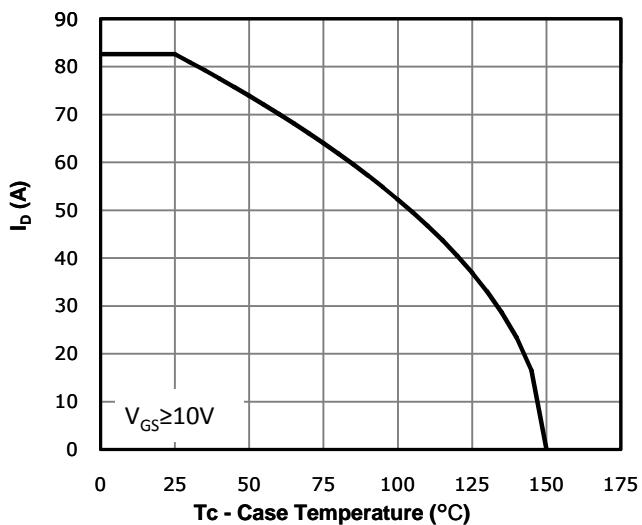


Fig 11: Safe Operating Area

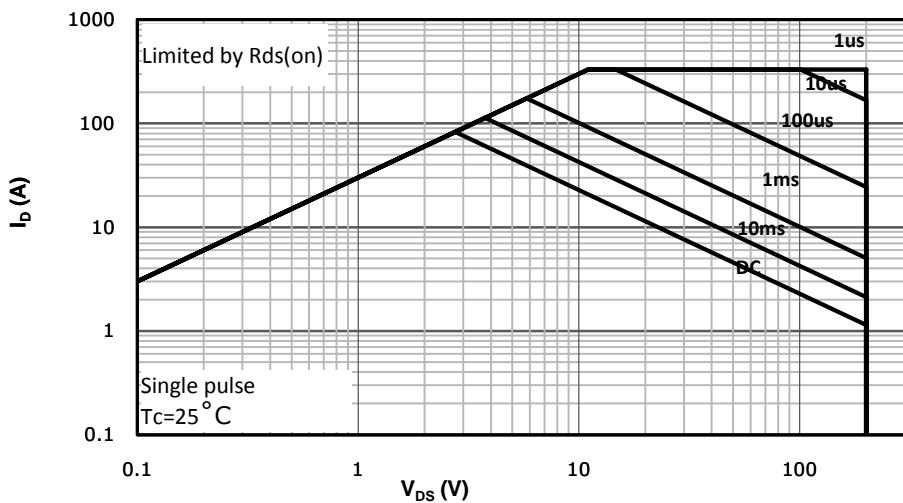
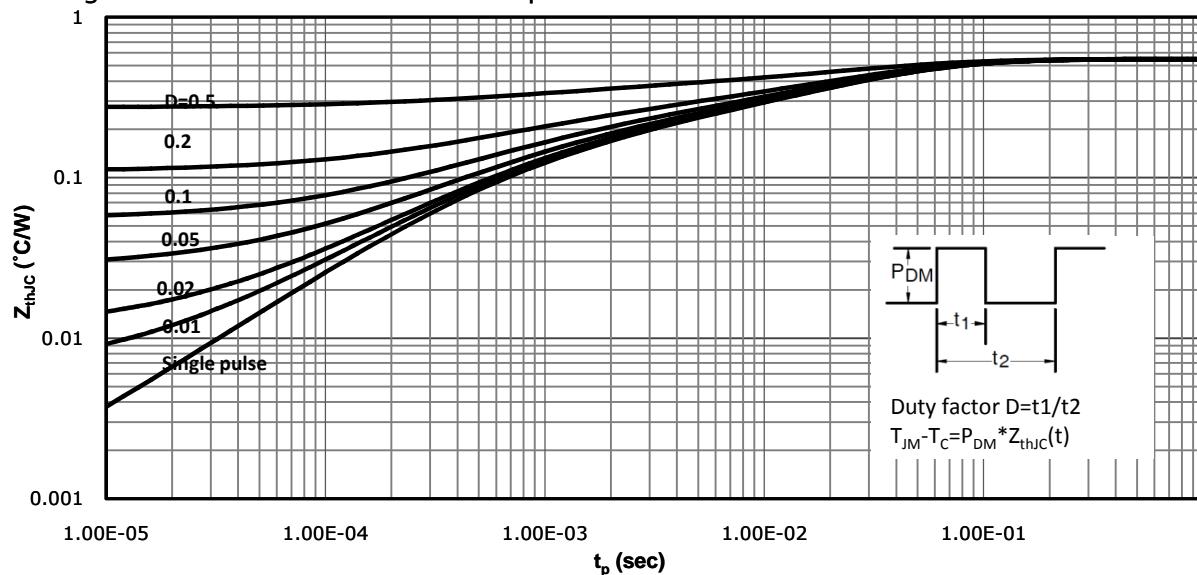
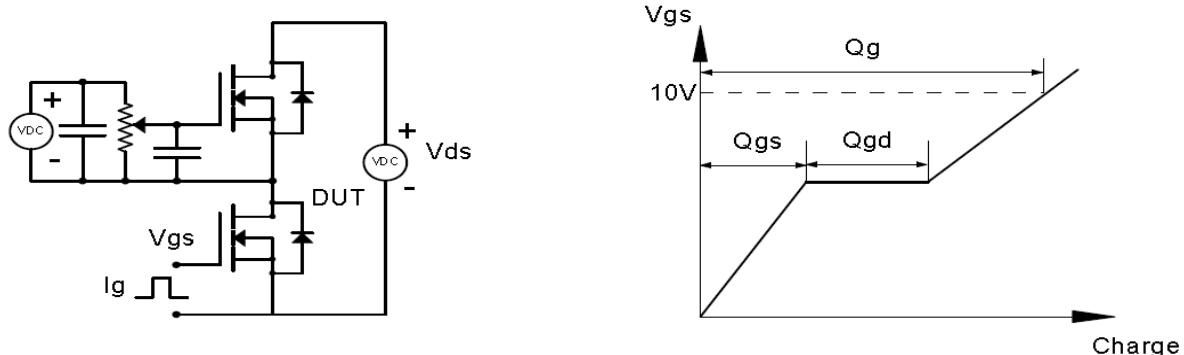


Fig 12: Max. Transient Thermal Impedance

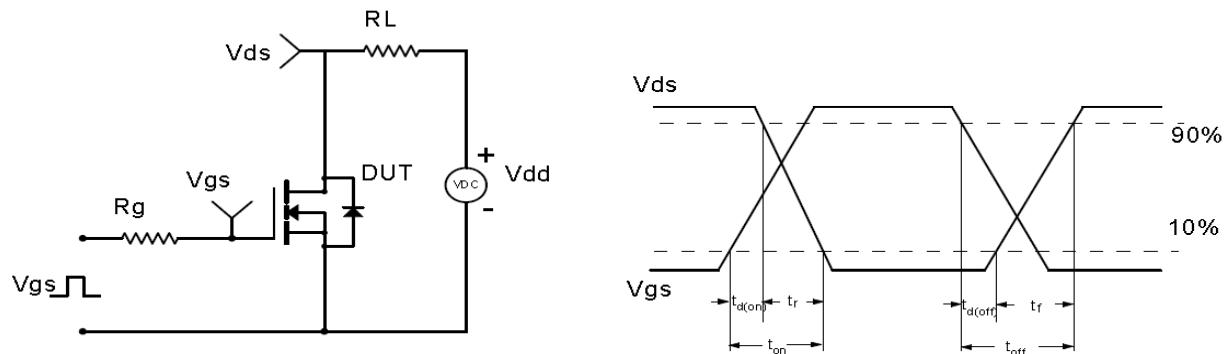


Test Circuit & Waveform

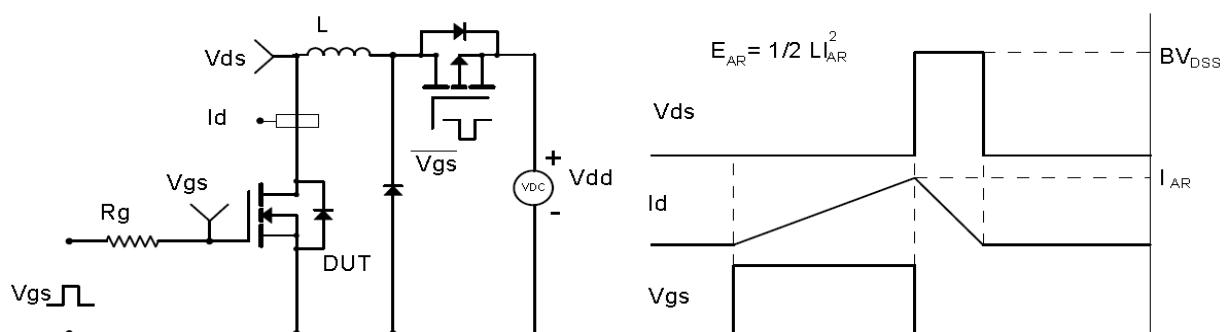
Gate Charge Test Circuit & Waveform



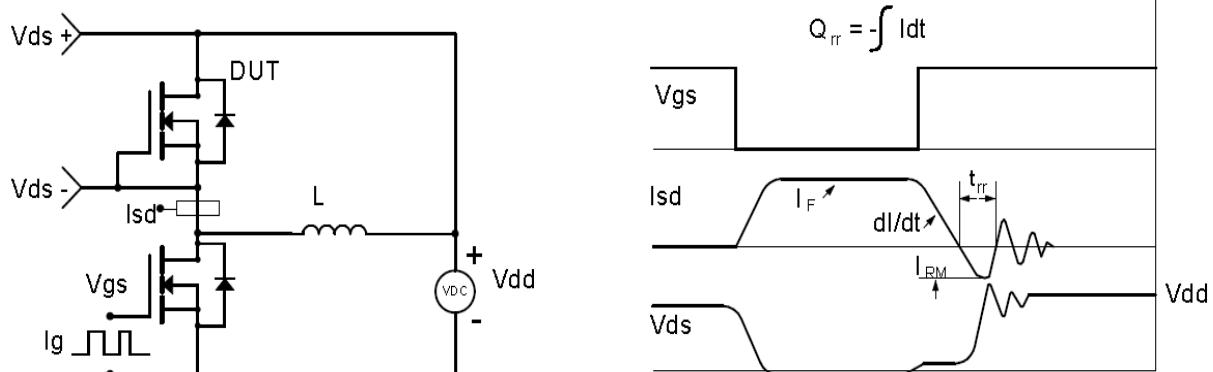
Resistive Switching Test Circuit & Waveforms



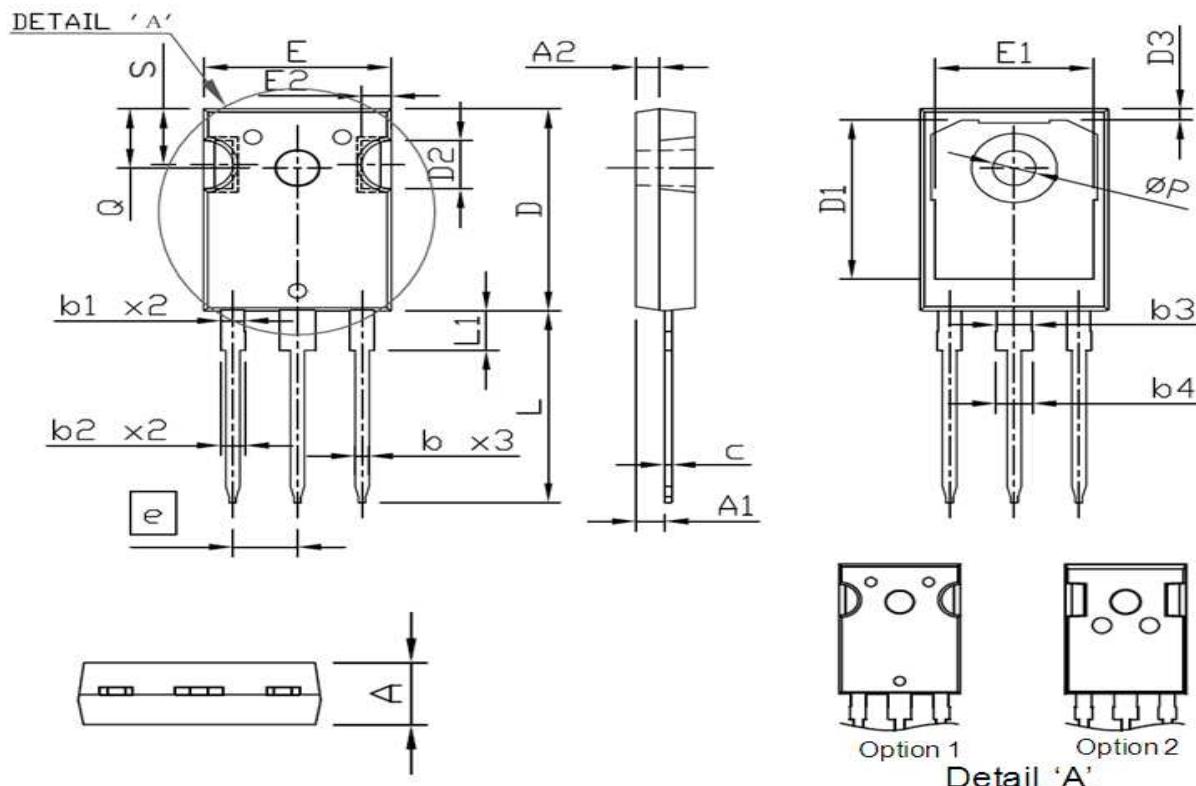
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: TO-247



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.85	5.15	0.191	0.203
A1	2.27	2.54	0.089	0.100
A2	1.90	2.10	0.075	0.083
b	1.07	1.33	0.042	0.052
b1	1.90	2.16	0.075	0.085
b2	2.00	2.21	0.079	0.087
b3	2.87	3.13	0.113	0.123
b4	2.87	3.20	0.113	0.126
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	3.68	5.10	0.145	0.201
D3	0.95	1.35	0.037	0.053
e	5.44 BSC.		0.214 BSC.	
E	15.70	16.13	0.618	0.635
E1	13.03	14.15	0.513	0.557
E2	2.20	2.60	0.087	0.102
L	19.72	20.32	0.776	0.800
L1	4.00	4.47	0.157	0.176
Q	6.04	6.30	0.238	0.248
P	3.50	3.70	0.138	0.146
S	5.49	6.00	0.216	0.236



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CRSQ155N20N3

SkyMOS3 N-MOSFET 200V, 13mΩ, 80A

Revision History

Revison	Date	Major changes
1.0	2021-11-20	Release of Preliminary version.

Disclaimer

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.

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